

**AMENDMENTS TO THE CLAIMS**

Please cancel Claim 6 and amend Claims 1, 5, 7, 9, 10, 12 and 24 as follows:

1. (Currently Amended) An apparatus, comprising:

a polishing chamber for polishing a conductive film made of copper which is formed on a substrate;

a cleaning chamber cleaning the polished substrate polished in the polishing chamber;

at least one drying chamber, having a first transferring port and a second transferring port, for drying the cleaned substrate transferred from the cleaning chamber through the first transferring port under a reduced pressure;

a film forming chamber forming a thin film on the substrate by a CVD method under the reduced pressure;

a transferring mechanism for receiving the dried substrate from the drying chamber through the second transferring port and for transferring the received substrate to the film forming chamber under the reduced pressure; and

a path for transferring the substrate between the transferring mechanism under the reduced pressure and a location outside the apparatus under an atmospheric pressure without passing through the drying chamber.

2. (Canceled)

3. (Canceled)

4. (Canceled)

5. (Currently amended) The apparatus as set forth in claim 1, further comprising

a conductive film forming chamber for forming a conductive film on the substrate formed with an insulating film having a recessed portion in a front face thereof so that the recessed portion is embedded with the conductive film made of copper;

wherein the substrate formed with the conductive film made of copper in the conductive film forming chamber is polished in the polishing chamber so that the conductive film made of

copper formed on the front face of the insulating film ~~except for the recessed portion~~ is polished away except for the recessed portion.

6. (Canceled)

7. (Currently Amended) The apparatus as set forth in claim [6] 1, wherein an inside of the drying chamber is in an inert gas atmosphere.

8. (Original) The apparatus as set forth in claim 7, wherein a plurality of the drying chambers are provided.

9. (Currently Amended) A film forming method, comprising the steps of:  
polishing a conductive film made of copper which is formed on ~~a~~ the substrate;  
cleaning and drying the polished substrate under a reduced pressure at a first position  
located in a first path, where the substrate is cleaned and dried ; and  
transferring the substrate to a second position for forming a thin film by a CVD method  
performed under ~~the~~ a reduced pressure through the first path and forming the thin film at the  
second position while maintaining the reduced-pressure state; and  
transferring the substrate under the reduced pressure to a location outside the apparatus  
under an atmospheric pressure through a second path different from the first path.

10. (Currently amended) The method as set forth in claim 9, further comprising the step of:

forming the conductive film made of copper on the substrate on which an insulating film having a recessed portion on a front face thereof is formed before the polishing step so that the recessed portion is embedded with the conductive film made of copper.

11. (Canceled)

12. (Currently Amended) An apparatus, comprising:  
a first substrate carrier for transferring a substrate in an atmospheric air;  
a first substrate processing portion performing a vacuum type processing on the substrate;

a second substrate processing portion performing a solution type processing on the substrate;

a first delivering and receiving portion having a first path for transferring ~~delivering and receiving~~ the substrate to be processed with the solution type processing between the second substrate processing portion and the first substrate processing portion; and

a second delivering and receiving portion having a second path for transferring ~~delivering and receiving~~ the substrate ~~not~~ to be processed with the vacuum type ~~solution type~~ processing between the first substrate carrier and the first substrate processing portion without passing through the second substrate processing portion.

13. (Previously Presented) The apparatus as set forth in claim 12, wherein the first substrate processing portion has a CVD film forming chamber.

14. (Previously Presented) The apparatus as set forth in claim 12, wherein the first substrate processing portion has an etching processing chamber.

15. (Previously Presented) The apparatus as set forth in claim 12, wherein the first substrate processing portion has a resist removing chamber.

16. (Previously Presented) The apparatus as set forth in claim 12, wherein the first substrate delivering and receiving portion has a mechanism of drying the substrate under a reduced pressure.

17. (Previously Presented) The apparatus as set forth in claim 12, further comprising:  
a second substrate carrier perpendicularly connected to the first substrate carrier and also connected to the first substrate delivering and receiving portion for transferring the substrate in an atmospheric air;

a polishing chamber disposed along the second substrate carrier, for polishing the substrate; and

a cleaning chamber disposed along the second substrate carrier, for cleaning the polished substrate.

18. (Previously Presented) The apparatus as set forth in claim 17, further comprising:  
a conductive film forming chamber, disposed along the second substrate carrier, for forming a conductive film on the substrate formed with an insulating film having a recessed portion in a front face thereof so that the recessed portion is embedded with the conductive film, wherein the substrate formed with the conductive film in the conductive film forming chamber is polished in the polishing chamber so that the conductive film formed on the front face of the insulating film except for the recessed portion is polished away.

19. (Canceled)

20. (Canceled)

21. (Canceled)

22. (Canceled)

23. (Previously Presented) The apparatus as set forth in claim 1, wherein the path is connected to the first transferring port.

24. (Currently amended) The apparatus as set forth in claim [1] 8, wherein [a] the plurality of drying chambers are stacked vertically.

25. (Previously Presented) The apparatus as set forth in claim 1, further comprising:  
an exhaust pipe for exhausting air from the at least one drying chamber.